N-CHANNEL ENHANCEMENT MODE POWER MOSFET

SI25N10

N-Channel Enhancement Mode Power MOSFET

Description

The SI25N10 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other switching application.

General Features

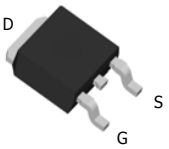
V_{DSS}	$R_{DS(ON)}$ @10V (typ)	I_D
100V	34mΩ	25A

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

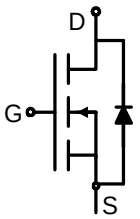
Application

- Battery switch
- DC/DC converter

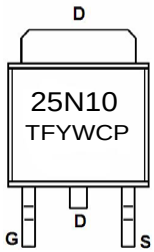
TO-252



Equivalent Circuit



MARKING



Y :year code W :week code

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±25	V
Drain Current-Continuous T_C=25℃	I_D	25	A
Drain Current-Continuous T_C=100℃		12	A
Drain Current-Pulsed (Note 1)	I_{DM}	60	A
Maximum Power Dissipation T_C=25℃	P_D	50	W
Maximum Power Dissipation T_C=100℃		20	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	2.3	℃/W

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

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Electrical Characteristics (T_C=25℃unless otherwise noted)

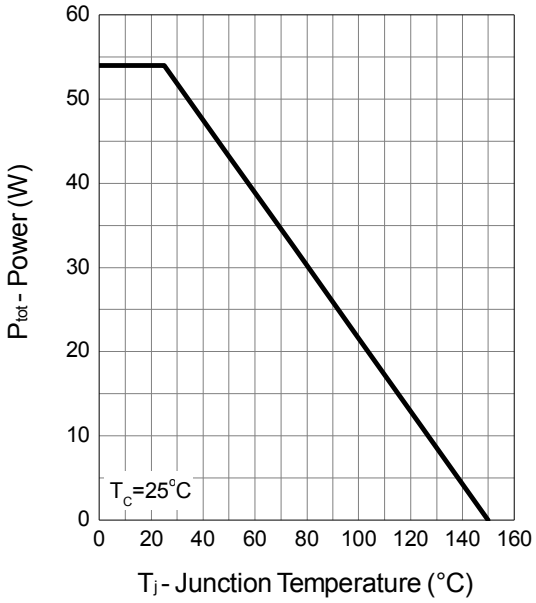
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	100	112		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V , V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±25V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.0	1.7	2.9	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=12A	-	30	34	mΩ
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=8A	-	32	36	mΩ
Forward Transconductance	g_{FS}	V_{DS}=25V,I_D=12A	5			S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=30V,V_{GS}=0V, F=1.0MHz	-	1350	-	PF
Output Capacitance	C_{oss}		-	150	-	PF
Reverse Transfer Capacitance	C_{rss}		-	35	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=30V,I_D=1A,R_L=30Ω V_{GS}=10V,R_G=6.0Ω	-	15	-	nS
Turn-on Rise Time	t_r		-	8.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	29	-	nS
Turn-Off Fall Time	t_f		-	9.5	-	nS
Total Gate Charge	Q_g	V_{DS}=50V,I_D=12A, V_{GS}=10V	-	23	-	nC
Gate-Source Charge	Q_{gs}		-	6	-	nC
Gate-Drain Charge	Q_{gd}		-	5.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=9.6A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	12	A
Reverse Recovery Time	t_{rr}	TJ = 25°C, IF =9.6A di/dt = 100A/μs (Note3)	-	21		nS
Reverse Recovery Charge	Qrr		-	97		nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

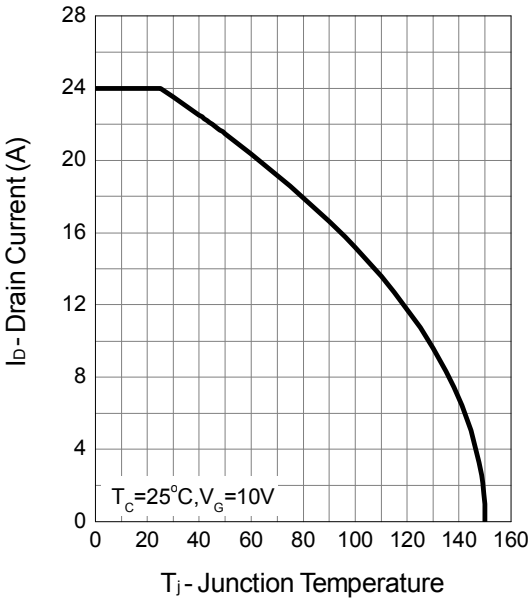
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Operating Characteristics

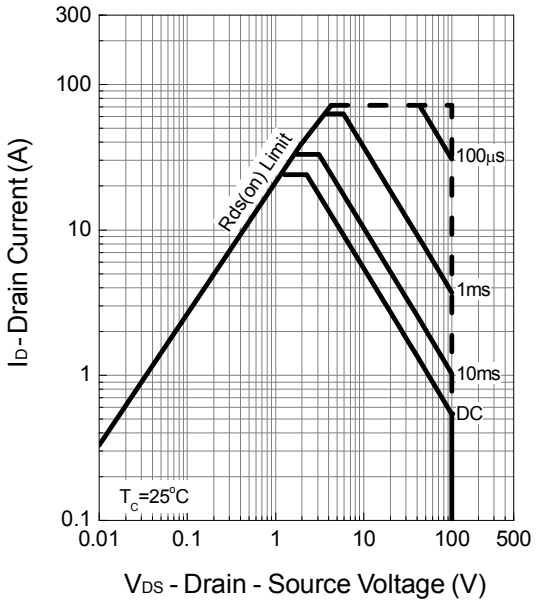
Power Dissipation



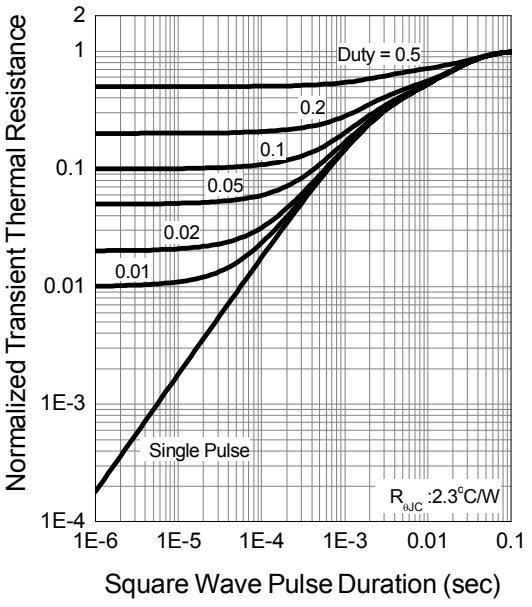
Drain Current



Safe Operation Area

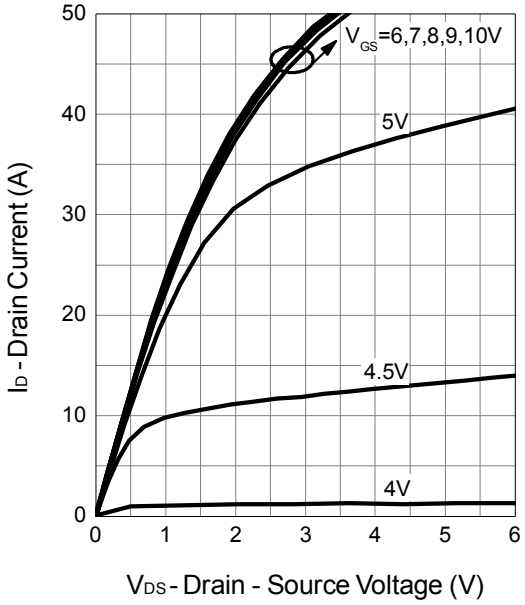


Thermal Transient Impedance

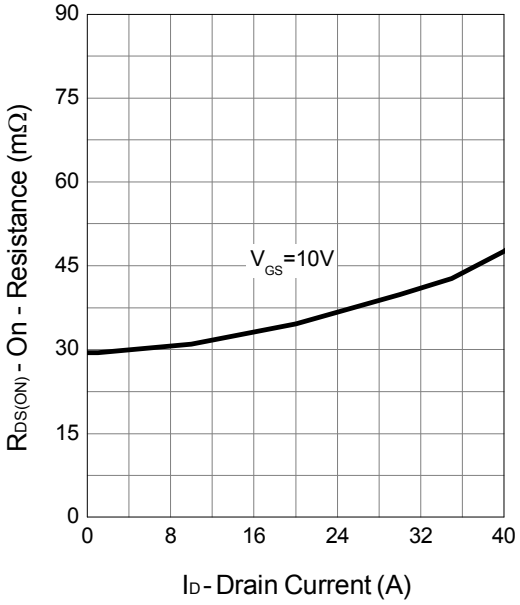


Typical Operating Characteristics (Cont.)

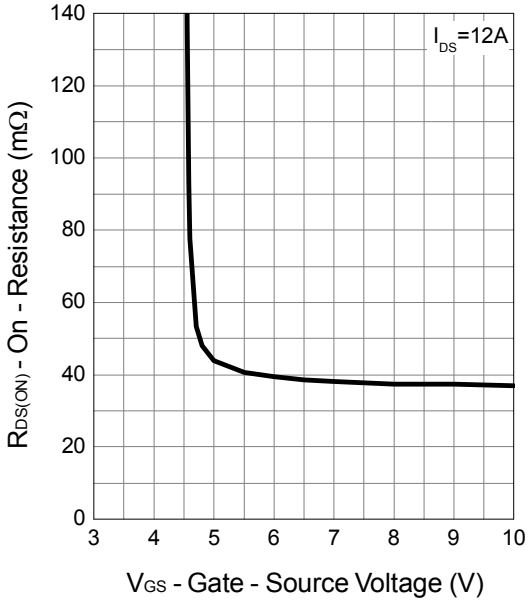
Output Characteristics



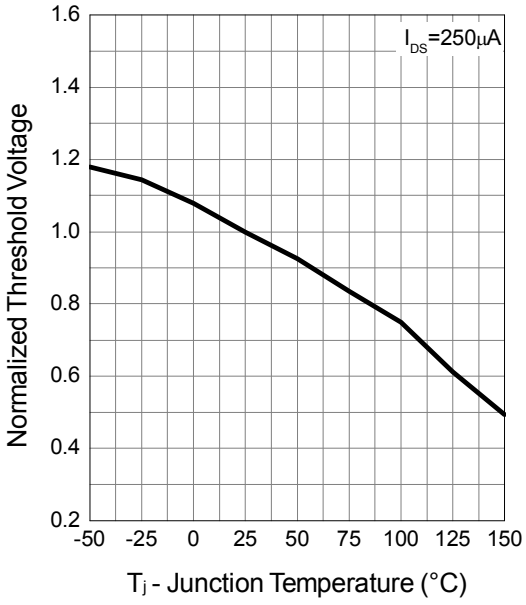
Drain-Source On Resistance



Gate-Source On Resistance

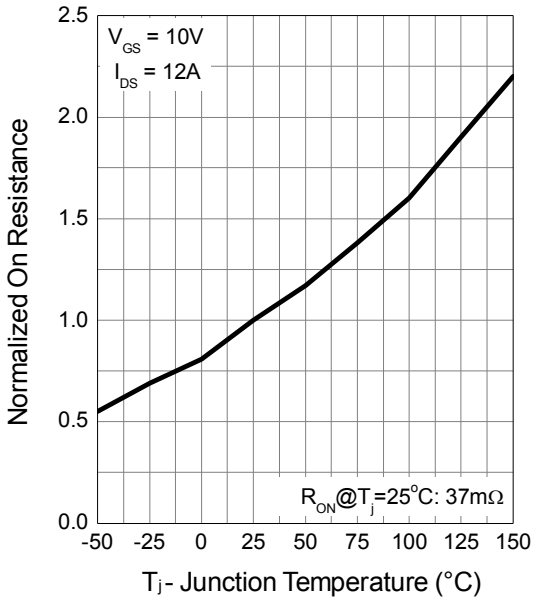


Gate Threshold Voltage

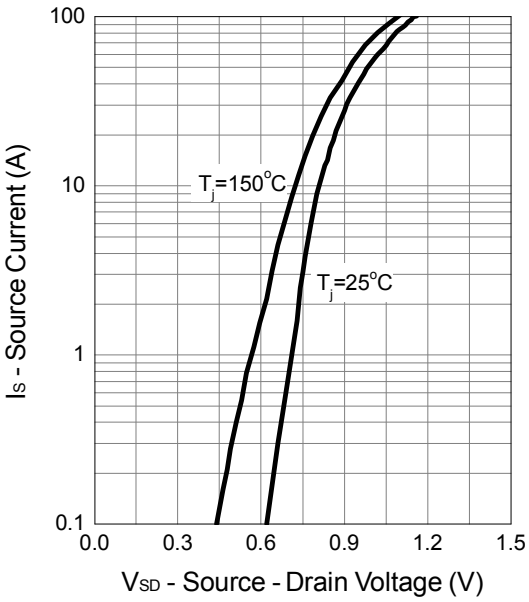


Typical Operating Characteristics (Cont.)

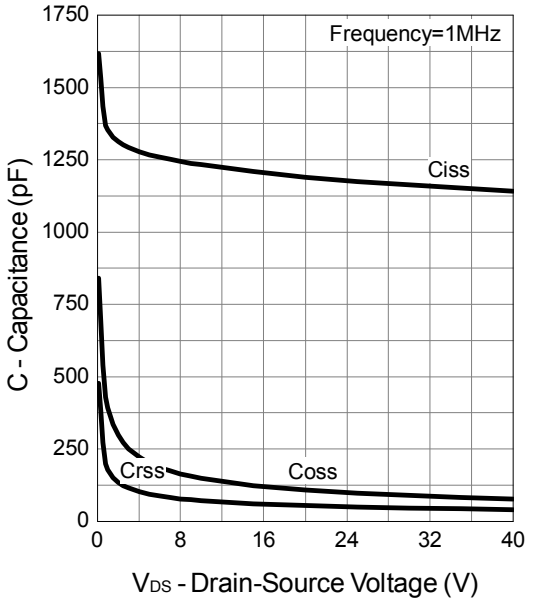
Drain-Source On Resistance



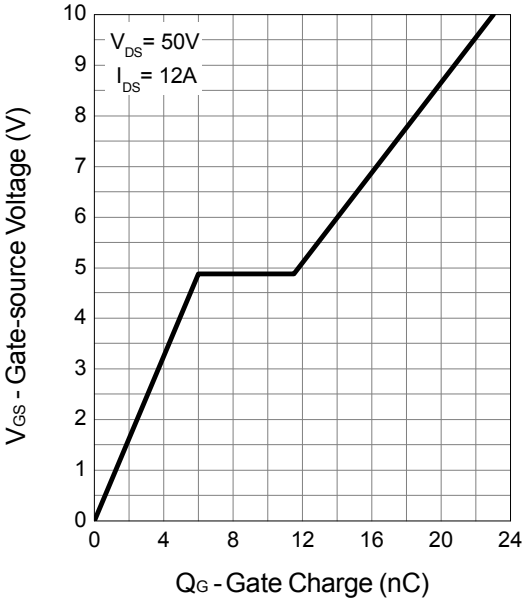
Source-Drain Diode Forward



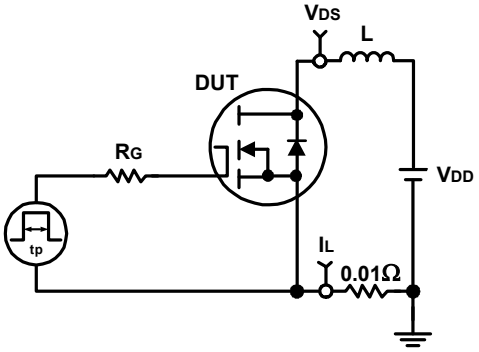
Capacitance

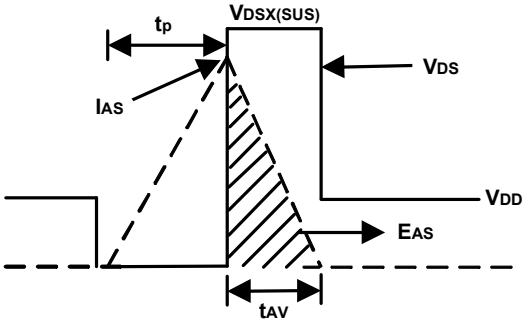


Gate Charge

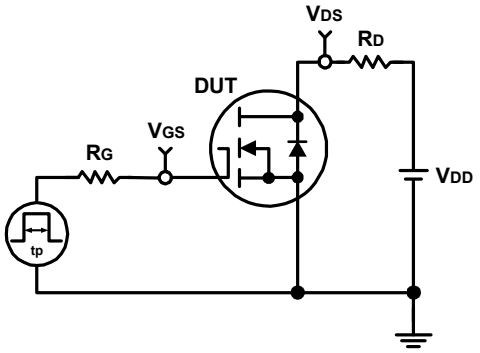


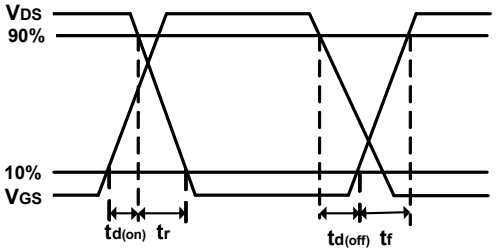
Avalanche Test Circuit and Waveforms





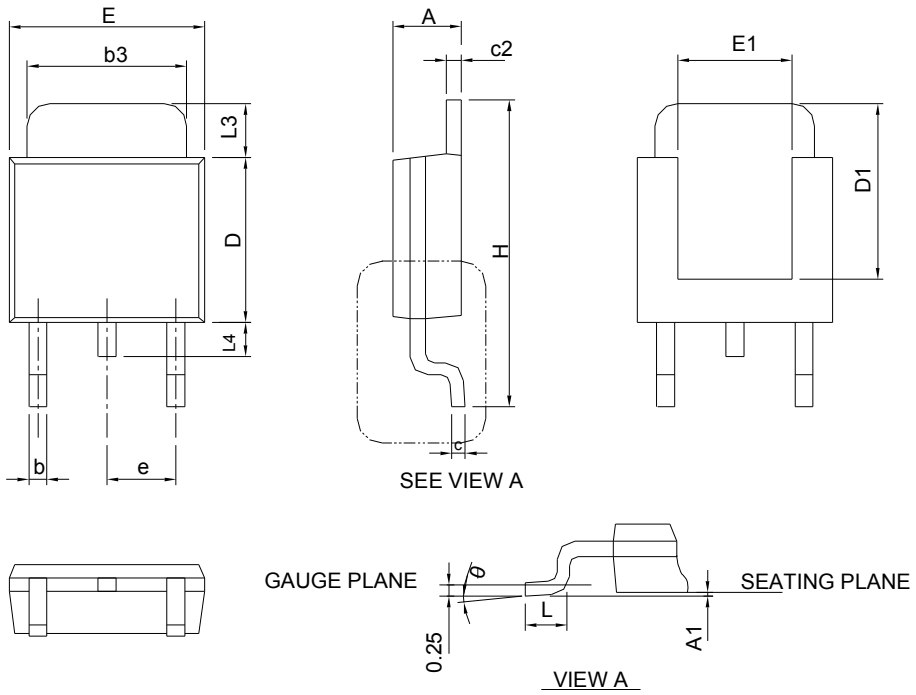
Switching Time Test Circuit and Waveforms





Package Information

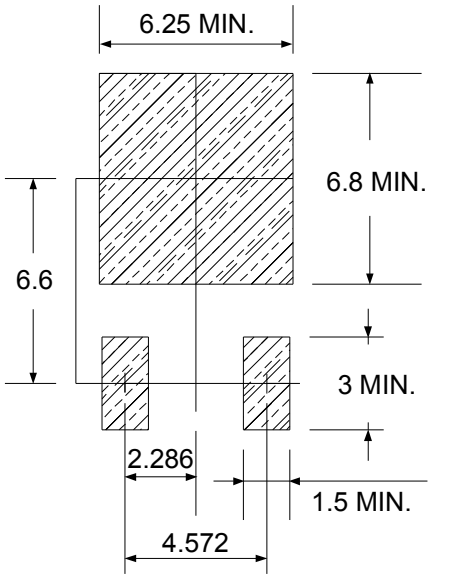
TO-252-2L



SYMBOL	TO-252-3			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1		0.13		0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4		1.02		0.040
θ	0°	8°	0°	8°

Note : Follow JEDEC TO-252 .

RECOMMENDED LAND PATTERN



UNIT: mm